



SOT-23 Plastic-Encapsulate Diodes

MMBD7000 SWITCHING DIODE

FEATURES

Power dissipation

P_D : 225 mW ($T_{amb}=25^{\circ}C$)

Forward Current

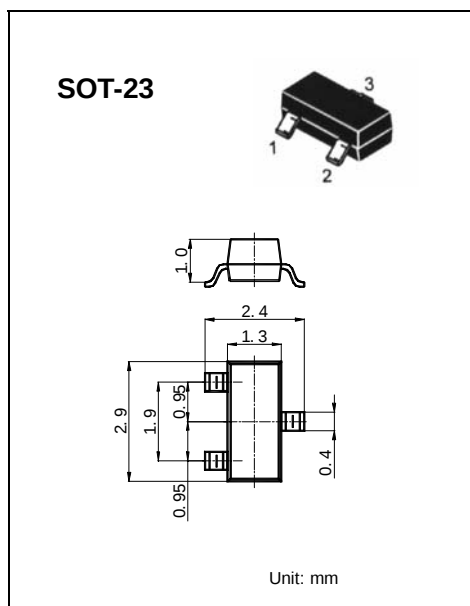
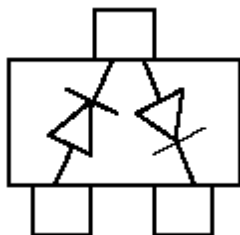
I_F : 200 mA

Reverse Voltage

V_R : 100 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	100		V
Reverse voltage leakage current	I_R	$V_R = 50V$ $V_R = 100V$ $V_R = 50V, 125^{\circ}C$		1.0 3.0 100	μA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 100mA$	0.55 0.67 0.75	0.7 0.82 1.1	V
Diode capacitance	C_D	$V_R = 0V$		1.5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 10mA$		4	nS

Marking	M5C
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